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4 Device Comparison

Table 4-1. Device Comparison

VERSION	TYPICAL THRESHOLD	TYPICAL HYSTERESIS	MAGNETIC RESPONSE	OUTPUT TYPE	SENSOR ORIENTATION	BANDWIDTH	PACKAGES AVAILABLE
TMAG5115A1C	1 mT	2 mT	Active Low	Open-drain	Z	60 kHz	SOT-23
TMAG5115B1C	3 mT	6 mT	Active Low	Open-drain	Z	60 kHz	SOT-23

5 Pin Configuration and Functions

For additional configuration information, see the [Mechanical, Packaging, and Orderable Information](#) section.

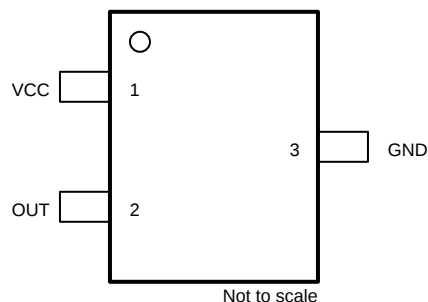


Figure 5-1. DBZ Package 3-Pin SOT-23 Top View

Table 5-1. Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
GND	3	GND	Ground pin
OUT	2	O	Hall sensor open-drain output. Requires a resistor pullup, typically 10 kΩ.
V _{CC}	1	P	Supply pin. 2.5 V to 26 V. TI recommends to use a minimum 0.01-μF capacitor.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Power supply voltage	–0.3	30	V
I _{SINK}	Output sink current		30	mA
Magnetic flux density, B _{MAX}		Unlimited	Unlimited	T
Junction temperature, T _J		–65	150	°C
Storage temperature, T _{stg}		–65	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged device model (CDM), ANSI/ESDA/ JEDEC JS-002 ⁽²⁾	±500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{CC}	Power supply voltage ⁽¹⁾	2.5	26	V
V _O	Output pin voltage	0	26	V
I _{SINK}	Output pin current sink	0	15	mA
T _A	Ambient temperature	–40	125	°C

- (1) Operating outside the [TMAG5115 Recommended Supply and Temperature Curve](#) can cause the device to enter a thermal shutdown state.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TMAG5115	UNIT
		DBZ (SOT-23)	
		3 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	208.2	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	102.3	°C/W
R _{θJB}	Junction-to-board thermal resistance	40.6	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	9.7	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	40.2	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	–	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

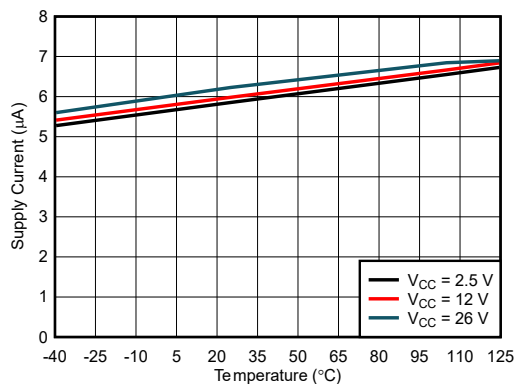
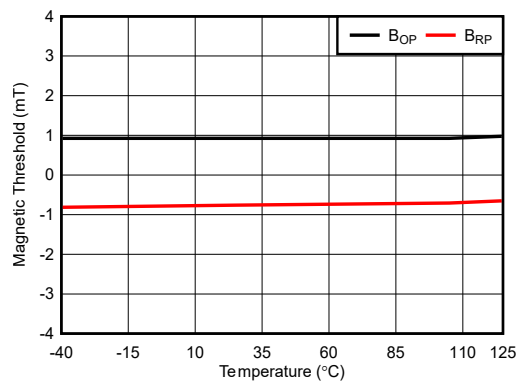
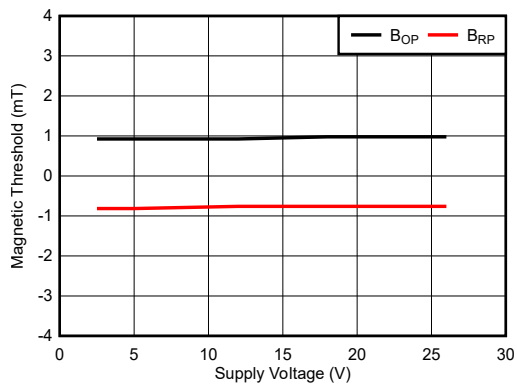
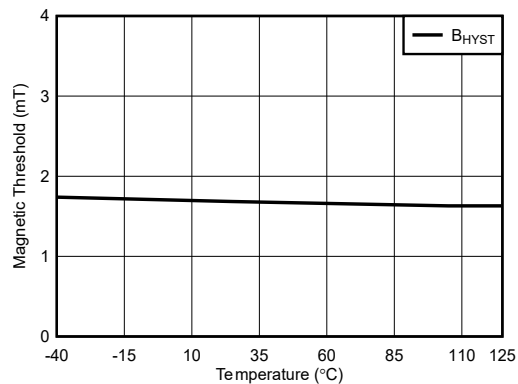
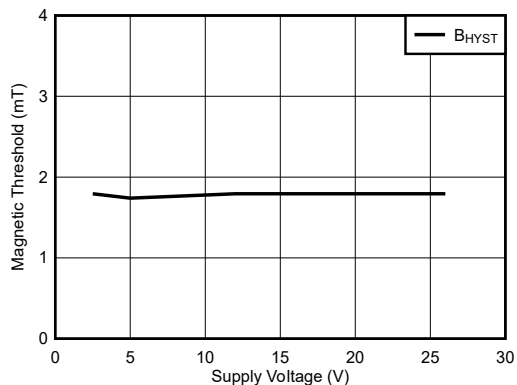
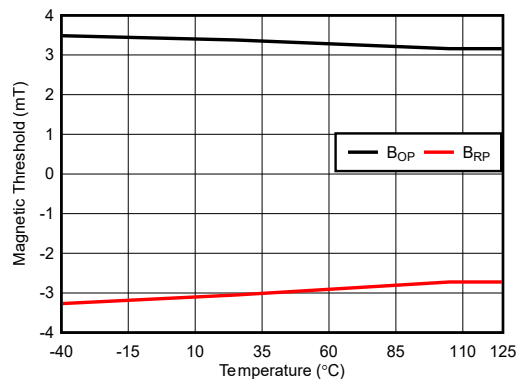
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLY						
I_{CC}	Operating supply current	$V_{CC} = 2.5\text{ V to }26\text{ V}$ $T_A = -40^\circ\text{C to }125^\circ\text{C}$		6	8	mA
t_{ON}	Power-on time			62.5		μs
P_{OS}	Power-on state	$V_{CC} > V_{CCmin}$ $t < t_{ON}$		High		
OUTPUT						
V_{OL}	Low-level output voltage	$I_{OL} = 5\text{ mA}$	0		0.7	V
I_{OH}	Output leakage current	$V_{CC} = 2.5\text{ V to }26\text{ V}$		0.1	1	μA
I_{SC}	Output short-circuit current protection		15	25	80	mA
t_R	Output rise time	$R_L = 10\text{ k}\Omega$ $C_L = 50\text{ pF}$ $V_{CC} = 12\text{ V}$		2		μs
t_F	Output fall time	$R_L = 10\text{ k}\Omega$ $C_L = 50\text{ pF}$ $V_{CC} = 12\text{ V}$		2		μs
t_{PD}	Propagation delay time			5	6	μs
Jitter	Output jitter window	1-kHz triangle magnetic wave with peak value at $\pm 8\text{ mT}$		5		μs
Jitter	Output jitter window	1-kHz square magnetic wave with peak value at $\pm 8\text{ mT}$		0.2		μs
Noise _{pp}	Internal Noise			125	200	μT
T_{SHUT}	Junction temperature shutdown threshold		156	168	180	$^\circ\text{C}$
T_{REC}	Junction temperature recovery threshold		131	143	155	$^\circ\text{C}$
FREQUENCY RESPONSE						
f_{CHOP}	Chopping frequency	TMAG5115xx		1000		kHz
f_{BW}	Signal bandwidth	TMAG5115xx		60		kHz

6.6 Magnetic Characteristics

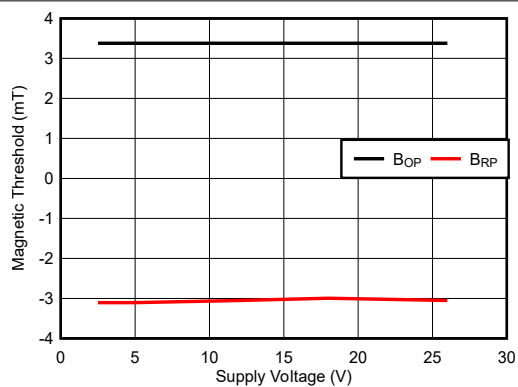
over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
TMAG5115A						
B _{OP}	Magnetic field operating point	V _{CC} = 2.5 V to 26 V	0.2	1	1.7	mT
B _{RP}	Magnetic field release point		−1.7	−1	−0.2	mT
B _{HYS}	Magnetic hysteresis B _{OP} - B _{RP}		0.4	2	3.4	mT
TMAG5115B						
B _{OP}	Magnetic field operating point	V _{CC} = 2.5 V to 26 V	2	3	4	mT
B _{RP}	Magnetic field release point		−4	−3	−2	mT
B _{HYS}	Magnetic hysteresis B _{OP} - B _{RP}		4	6	8	mT

6.7 Typical Characteristics

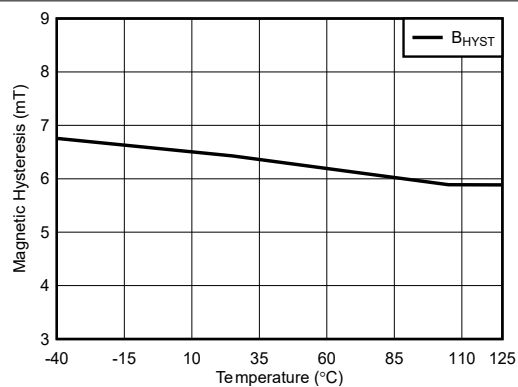
Figure 6-1. I_{CC} vs T_A  $V_{CC} = 12\text{ V}$ Figure 6-2. TMAG5115A B_{OP} and B_{RP} vs T_A  $T_A = 25^\circ\text{C}$ Figure 6-3. TMAG5115A B_{OP} and B_{RP} vs V_{CC}  $V_{CC} = 12\text{ V}$ Figure 6-4. TMAG5115A B_{HYST} vs T_A  $T_A = 25^\circ\text{C}$ Figure 6-5. TMAG5115A B_{HYST} vs V_{CC}  $V_{CC} = 12\text{ V}$ Figure 6-6. TMAG5115B B_{OP} and B_{RP} vs T_A

6.7 Typical Characteristics (continued)



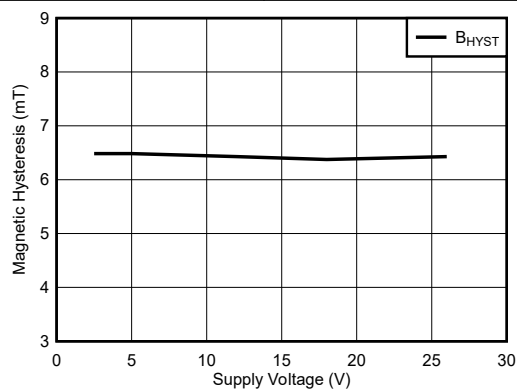
$T_A = 25^\circ\text{C}$

Figure 6-7. TMAG5115B B_{OP} and B_{RP} vs V_{CC}



$V_{CC} = 12\text{ V}$

Figure 6-8. TMAG5115B B_{HYST} vs T_A



$T_A = 25^\circ\text{C}$

Figure 6-9. TMAG5115B B_{HYST} vs V_{CC}

7 Detailed Description

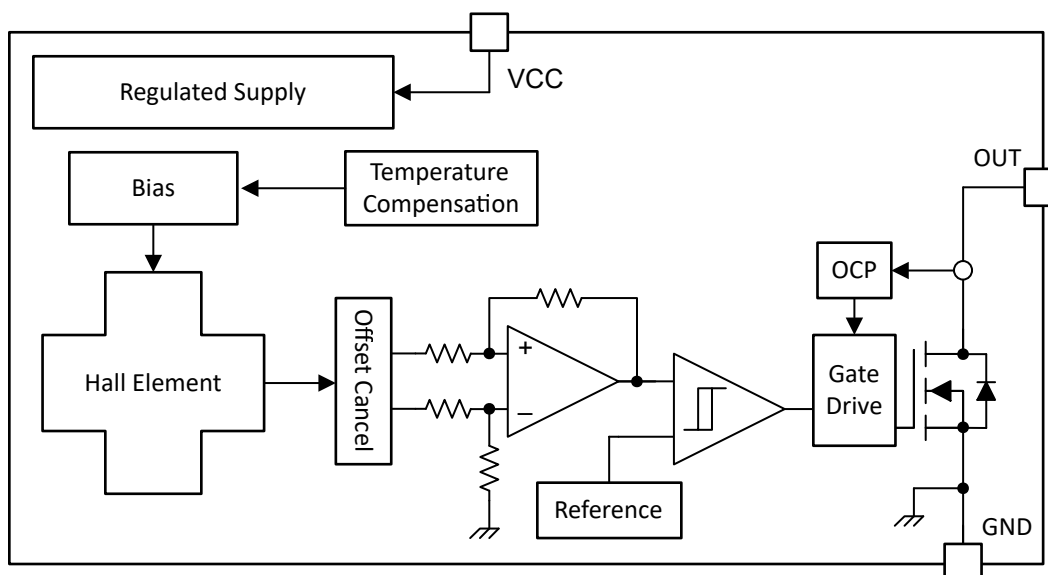
7.1 Overview

The TMAG5115 is a chopper-stabilized Hall sensor with a digital latched output for magnetic sensing applications. The TMAG5115 device can be powered with a supply voltage between 2.5 V and 26 V. The field polarity is defined as follows: a south pole near the marked side of the package is a positive magnetic field, and a north pole near the marked side of the package is a negative magnetic field.

The output state is dependent on the magnetic field perpendicular to the package. A south pole near the marked side of the package causes the output to pull low (operate point, B_{OP}), and a north pole near the marked side of the package causes the output to release (release point, B_{RP}). Hysteresis is included in between the operate point and the release point therefore magnetic-field noise does not accidentally trip the output.

An external pullup resistor is required on the OUT pin. The OUT pin can be pulled up to V_{CC} or to a different voltage supply to allow for easier interfacing with controller circuits.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Field Direction Definition

Figure 7-1 shows the positive magnetic field defined as a south pole near the marked side of the package and the negative magnetic field defined as a north pole near the marked side of the package.

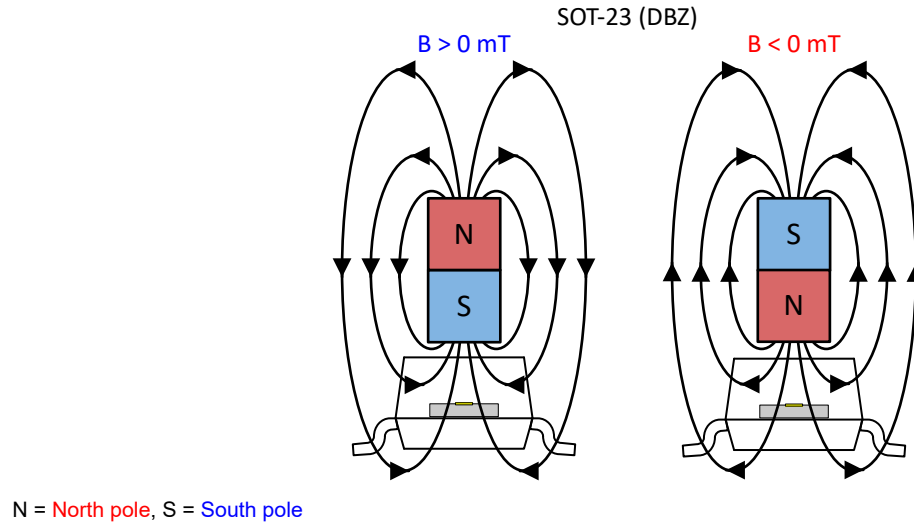


Figure 7-1. Field Direction Definition

7.3.2 Device Output

If the device is powered on with a magnetic field strength between B_{RP} and B_{OP} , then the device output is indeterminate and can either be Hi-Z or low. If the field strength is greater than B_{OP} , then the output is pulled low. If the field strength is less than B_{RP} , then the output is released.

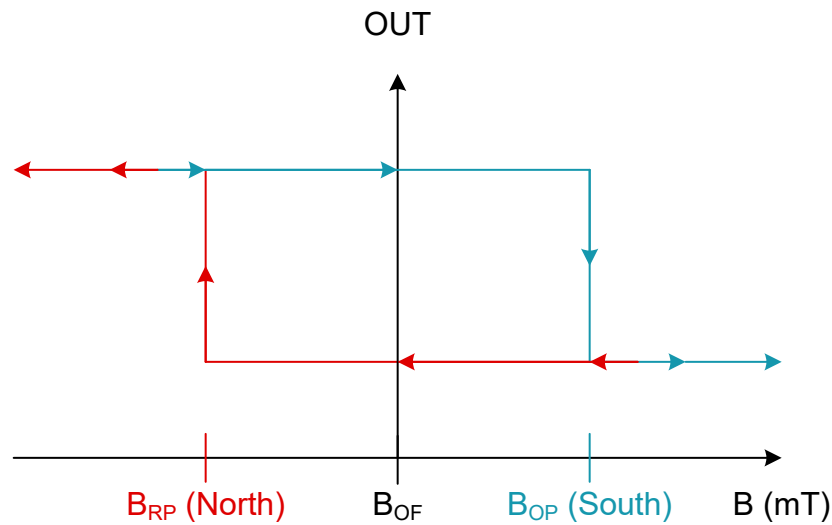


Figure 7-2. TMAG5115 $B_{OP} > 0$

7.3.3 Power-On Time

After applying V_{CC} to the TMAG5115, t_{on} must elapse before the OUT pin is valid. During the power-up sequence, the output is Hi-Z. A pulse as shown in Figure 7-3 and Figure 7-4 occurs at the end of t_{on} . This pulse can allow the host processor to determine when the TMAG5115 output is valid after start-up. In Case 1 (Figure 7-3) and Case 2 (Figure 7-4), the output is defined assuming a constant magnetic field $B > B_{OP}$ and $B < B_{RP}$.

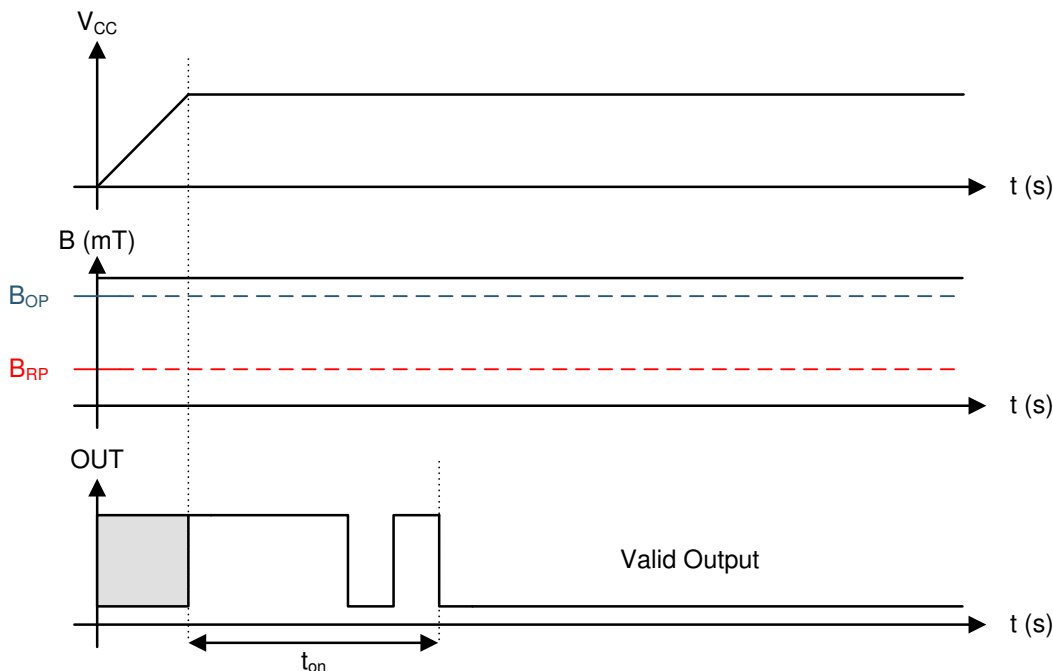


Figure 7-3. Case 1: Power On When $B > B_{OP}$

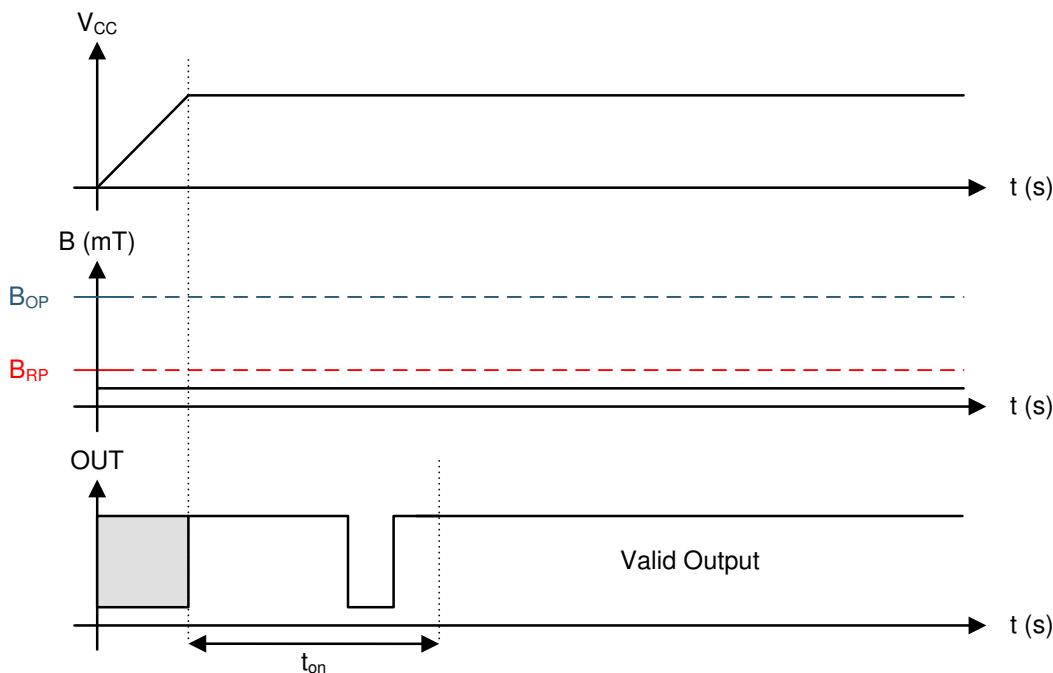


Figure 7-4. Case 2: Power On When $B < B_{RP}$

If the device is powered on with the magnetic field strength $B_{RP} < B < B_{OP}$, then the device output is indeterminate and can either be Hi-Z or pulled low. During the power-up sequence, the output is held Hi-Z until t_{on} has elapsed. At the end of t_{on} , a pulse is given on the OUT pin to indicate that t_{on} has elapsed. After t_{on} , if the magnetic field changes such that $B_{OP} < B$, the output is released. Case 3 (Figure 7-5) and Case 4 (Figure 7-6) show examples of this behavior.

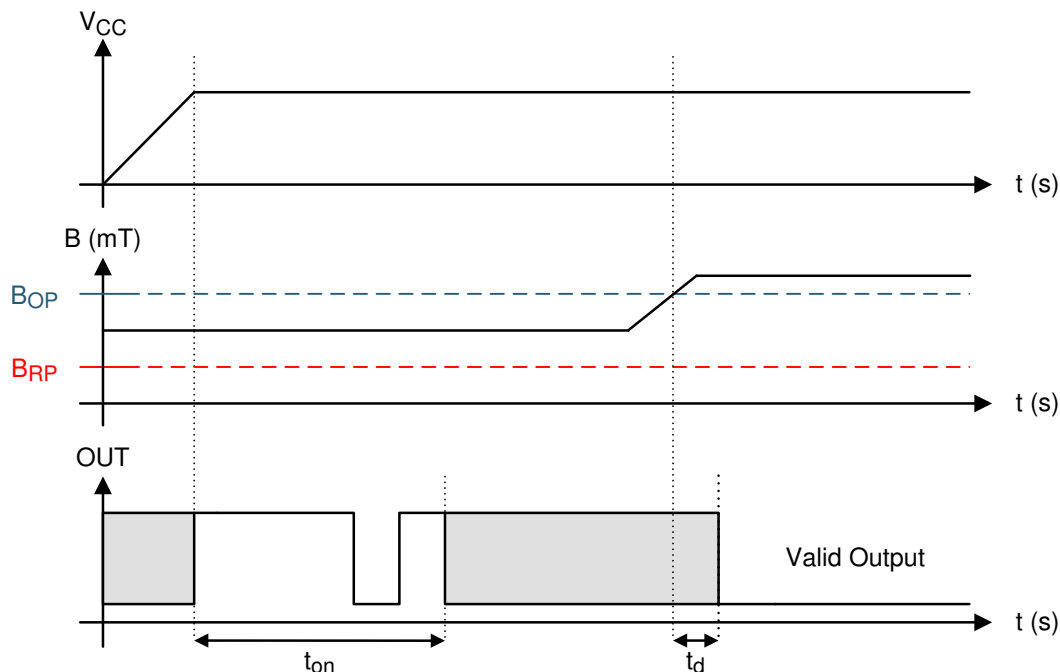


Figure 7-5. Case 3: Power On When $B_{RP} < B < B_{OP}$, Followed by $B > B_{OP}$

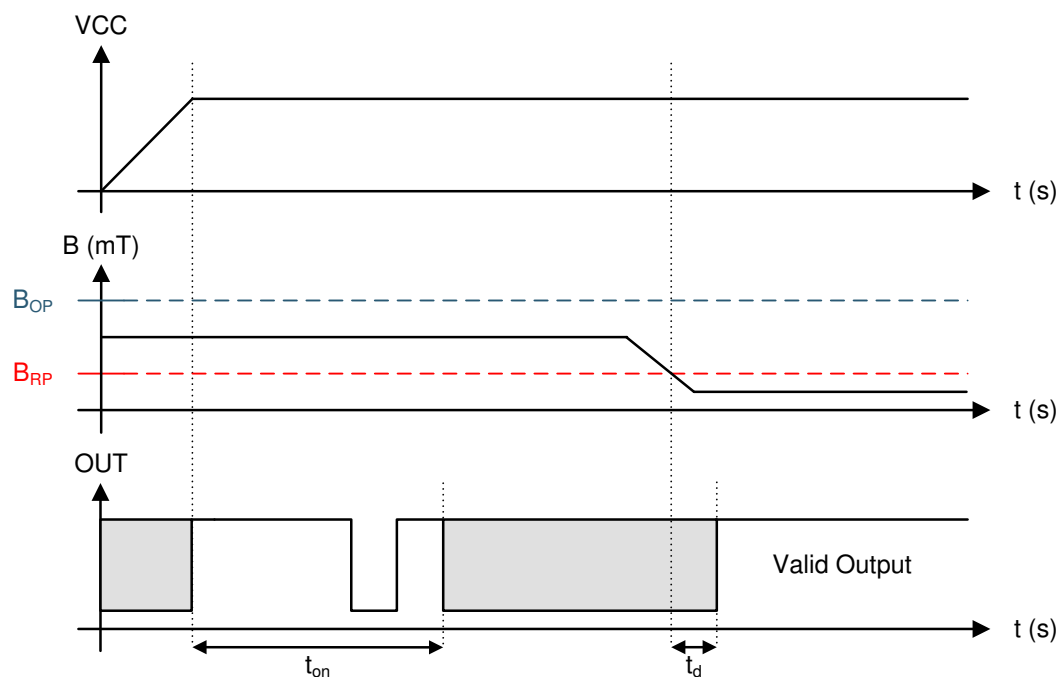


Figure 7-6. Case 4: Power On When $B_{RP} < B < B_{OP}$, Followed by $B < B_{RP}$

7.3.4 Output Stage

Figure 7-7 shows the TMAG5115 open-drain NMOS output structure, rated to sink up to 15 mA of current.

Note

V_{ref} is not restricted to V_{CC} . The allowable voltage range of this pin is specified in the [Recommended Operating Conditions](#).

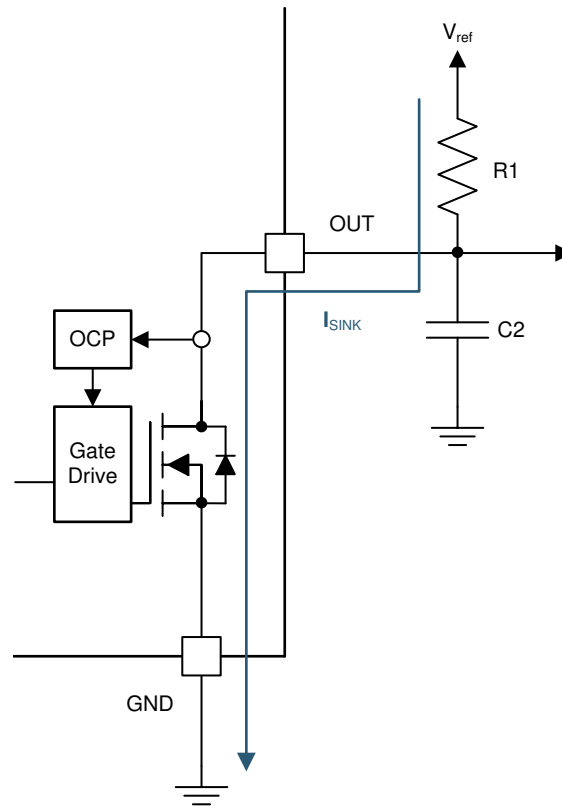


Figure 7-7. NMOS Open-Drain Output

Select a value for C2 based on the system bandwidth specifications as shown in [Equation 1](#).

$$2 \times f_{BW} \text{ (Hz)} < \frac{1}{2\pi \times R1 \times C2} \quad (1)$$

Most applications do not require this C2 filtering capacitor.

7.3.5 Protection Circuits

The TMAG5115 device is fully protected against overcurrent and overtemperature conditions. [Table 7-1](#) lists a summary of the protection circuits.

Table 7-1. Protection Circuit Summary

FAULT	CONDITION	DEVICE	DESCRIPTION	RECOVERY
FET overload	$I_{\text{SINK}} \geq I_{\text{SC}}$	Operating	Output current is clamped to I_{SC}	$I_{\text{SINK}} < I_{\text{SC}}$
Overtemperature	$T_J \geq 156^\circ\text{C}$	Operating	Device shuts down until recovery temperature is reached	$T_J \leq 156^\circ\text{C}$

7.3.5.1 Short-Circuit Protection

An analog current-limit circuit limits the current through the FET. The driver current is clamped to I_{SC} . During this clamping, the $r_{\text{DS(on)}}$ of the output FET is increased from the nominal value.

7.3.5.2 Overtemperature Protection

The TMAG5115 features overtemperature protection to prevent damage to the device and system in the case of runaway thermal heating. If the output is short-circuited, there will be greater power dissipation through the device causing the junction temperature to rise. If the temperature rises to above the limits specified in the [Electrical Characteristics](#) table, the device will enter a thermal shutdown and the OUT pin will turn to Hi-Z regardless of the current magnetic field detected.

The TMAG5115 thermal shutdown can be differentiated from normal operation by viewing the supply current into the device. While in thermal shutdown, the supply current is lower than normal operation.

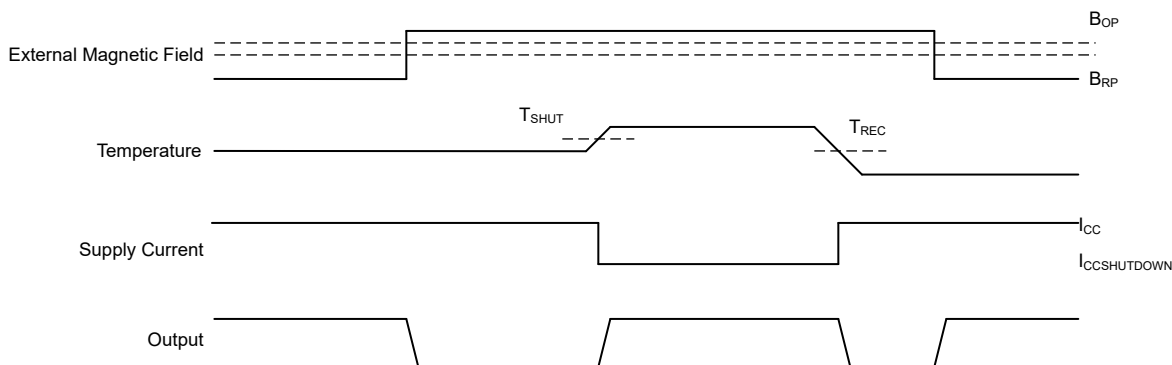


Figure 7-8. TMAG5115 Overtemperature Protection Diagram

The TMAG5115 can support a supply voltage of 2.5 V to 26 V. Higher temperature and supply conditions can increase the junction temperature of the device, however, which can exceed the thermal shutdown limit. This can cause a device shutdown. TI recommends to not exceed a temperature and supply combination shown in [Figure 7-9](#).

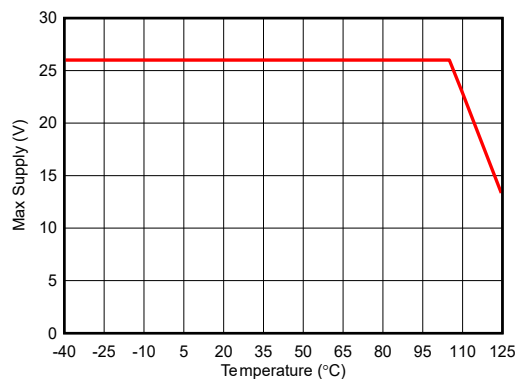


Figure 7-9. TMAG5115 Recommended Supply and Temperature Curve

7.4 Device Functional Modes

The TMAG5115 is active only when V_{CC} is between 2.5 V and 26 V and T_J is less than 156°C.

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The TMAG5115 is used in magnetic position sensing applications. The device features a high-speed architecture to facilitate precise field measurement. With latching magnetic characteristics, the output is turned low or high respectively with a sufficiently strong south or north pole facing the package top side. When removing the magnetic field, the device keeps its previous state.

For reliable functionality, the magnet must apply a flux density at the sensor greater than the corresponding maximum B_{OP} or B_{RP} numbers specified in the [Magnetic Characteristics](#) table. Add additional margin to account for mechanical tolerance, temperature effects, and magnet variation.

8.2 Typical Applications

8.2.1 Standard Circuit

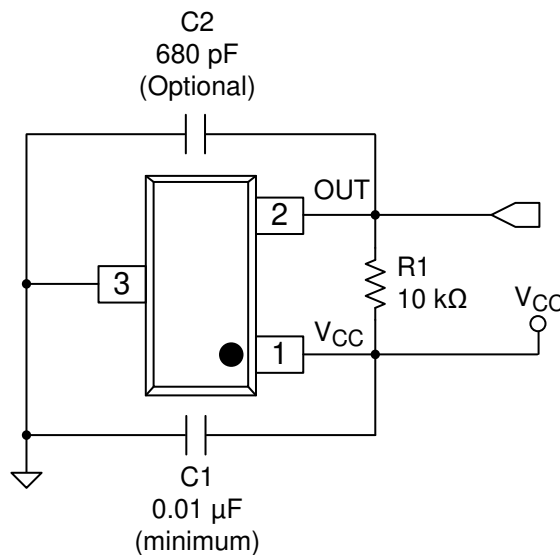


Figure 8-1. Typical Application Circuit

8.2.1.1 Design Requirements

For this design example, use the parameters listed in [Table 8-1](#) as the input parameters.

Table 8-1. Design Parameters

DESIGN PARAMETER	REFERENCE	EXAMPLE VALUE
Supply voltage	V_{CC}	3.0 V to 3.6 V
System bandwidth	f_{BW}	10 kHz

8.2.1.2 Detailed Design Procedure

Table 8-2. External Components

COMPONENT	PIN 1	PIN 2	RECOMMENDED
C1	V _{CC}	GND	A 0.01-μF (minimum) ceramic capacitor rated for V _{CC}
C2	OUT	GND	Optional: Place a ceramic capacitor to GND
R1	OUT	REF ⁽¹⁾	Requires a resistor pullup

(1) REF is not a pin on the TMAG5115 device, but a REF supply-voltage pullup is required for the OUT pin. The OUT pin may be pulled up to V_{CC}.

8.2.1.2.1 Configuration Example

In a 3.3-V system, $3.0\text{ V} \leq V_{\text{ref}} \leq 3.6\text{ V}$. Use [Equation 2](#) to calculate the allowable range for R1.

$$\frac{V_{\text{ref max}}}{30\text{ mA}} \leq R1 \leq \frac{V_{\text{ref min}}}{100\text{ }\mu\text{A}} \quad (2)$$

For this design example, use [Equation 3](#) to calculate the allowable range of R1.

$$\frac{3.4\text{ V}}{30\text{ mA}} \leq R1 \leq \frac{3.2\text{ V}}{100\text{ }\mu\text{A}} \quad (3)$$

Therefore:

$$120\text{ }\Omega \leq R1 \leq 30\text{ k}\Omega \quad (4)$$

After finding the allowable range of R1 ([Equation 4](#)), select a value between 500 Ω and 32 k Ω for R1.

Assuming a system bandwidth of 10 kHz, use [Equation 5](#) to calculate the value of C2.

$$2 \times f_{\text{BW}} (\text{Hz}) < \frac{1}{2\pi \times R1 \times C2} \quad (5)$$

For this design example, use [Equation 6](#) to calculate the value of C2.

$$2 \times 10\text{ kHz} < \frac{1}{2\pi \times R1 \times C2} \quad (6)$$

An R1 value of 10 k Ω and a C2 value less than 820 pF satisfy the requirement for a 10-kHz system bandwidth.

A selection of R1 = 10 k Ω and C2 = 680 pF can cause a low-pass filter with a corner frequency of 23.4 kHz.

8.2.1.3 Application Curves

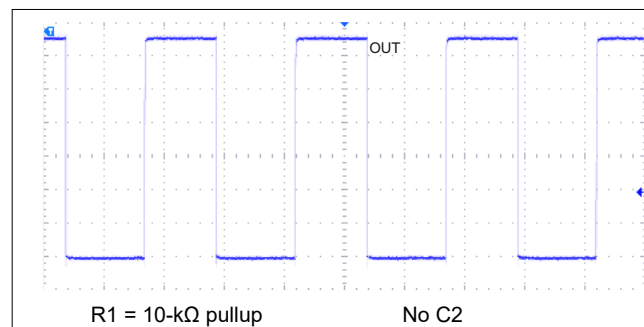


Figure 8-2. 10-kHz Switching Magnetic Field

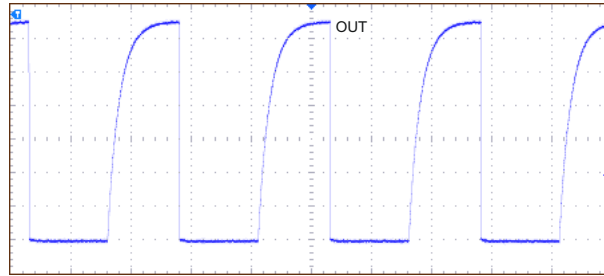


Figure 8-3. 10-kHz Switching Magnetic Field

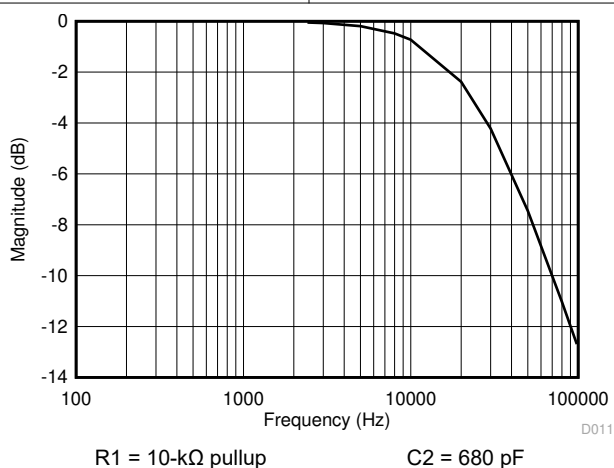


Figure 8-4. Low-Pass Filtering

8.3 Power Supply Recommendations

The TMAG5115 device is designed to operate from an input voltage supply range between 2.5 V and 26 V. A recommended 0.1- μ F ceramic capacitor rated for V_{CC} must be placed as close to the TMAG5115 as possible. Bypass capacitor values larger than 0.1 μ F may be required to attenuate any significant high-frequency ripple and noise components generated by the power source. TI recommends limiting the supply voltage variation to less than 50 mV_{PP}.

8.4 Layout

8.4.1 Layout Guidelines

TI recommends placing the bypass capacitor near the TMAG5115 device for efficient power delivery with minimal inductance. TI recommends placing the external pullup resistor near the microcontroller input to provide the most stable voltage at the input. Alternatively, an integrated pullup resistor within the GPIO of the microcontroller can be used.

Generally, using PCB copper planes underneath the TMAG5115 device has no effect on magnetic flux and does not interfere with device performance. This is because copper is not a ferromagnetic material. However, nearby system components that contain iron or nickel can redirect magnetic flux in unpredictable ways.

8.4.2 Layout Example

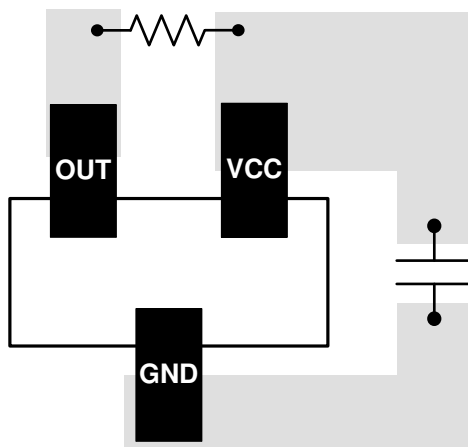


Figure 8-5. TMAG5115 Layout Example

9 Device and Documentation Support

9.1 Device Support

9.1.1 Hall Sensor Location

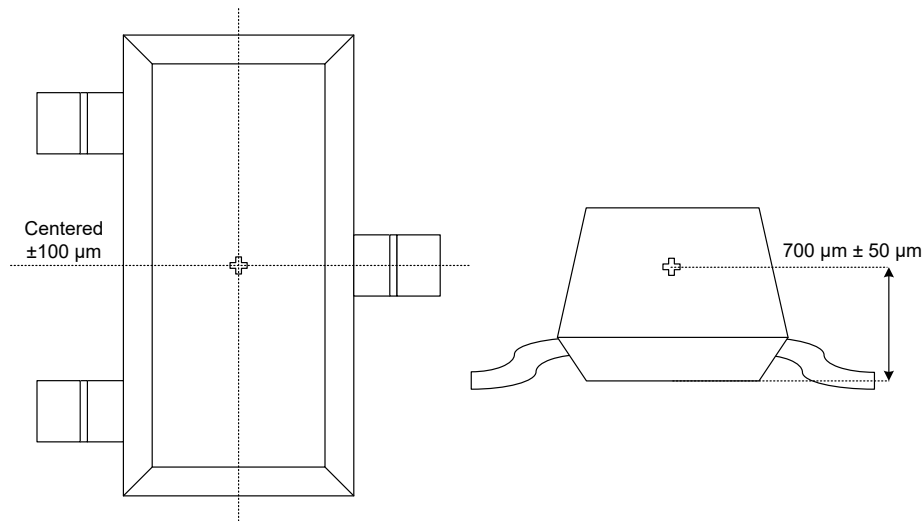


Figure 9-1. Hall Sensor Location (Not to Scale)

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

[TI Glossary](#)

This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (February 2023) to Revision B (August 2024)	Page
• Removed unit spacing between measurement units and values.....	1
• Changed <i>Device Information</i> table to <i>Package Information</i>	1
• Changed the typical threshold and typical hysteresis values in the <i>Device Comparison</i> table to correctly match the values found in the <i>Magnetic Characteristics</i> table.....	3

Changes from Revision * (December 2022) to Revision A (February 2023)	Page
• Added <i>Device Comparison</i> table.....	3
• Added TMAG5115A magnetic specifications.....	5
• Added typical characteristic curves for TMAG5115A.....	6

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TMAG5115A1CQDBZR	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	15A1
TMAG5115A1CQDBZR.A	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	15A1
TMAG5115B1CQDBZR	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	15B1
TMAG5115B1CQDBZR.A	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	15B1

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TMAG5115A1CQDBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TMAG5115B1CQDBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS

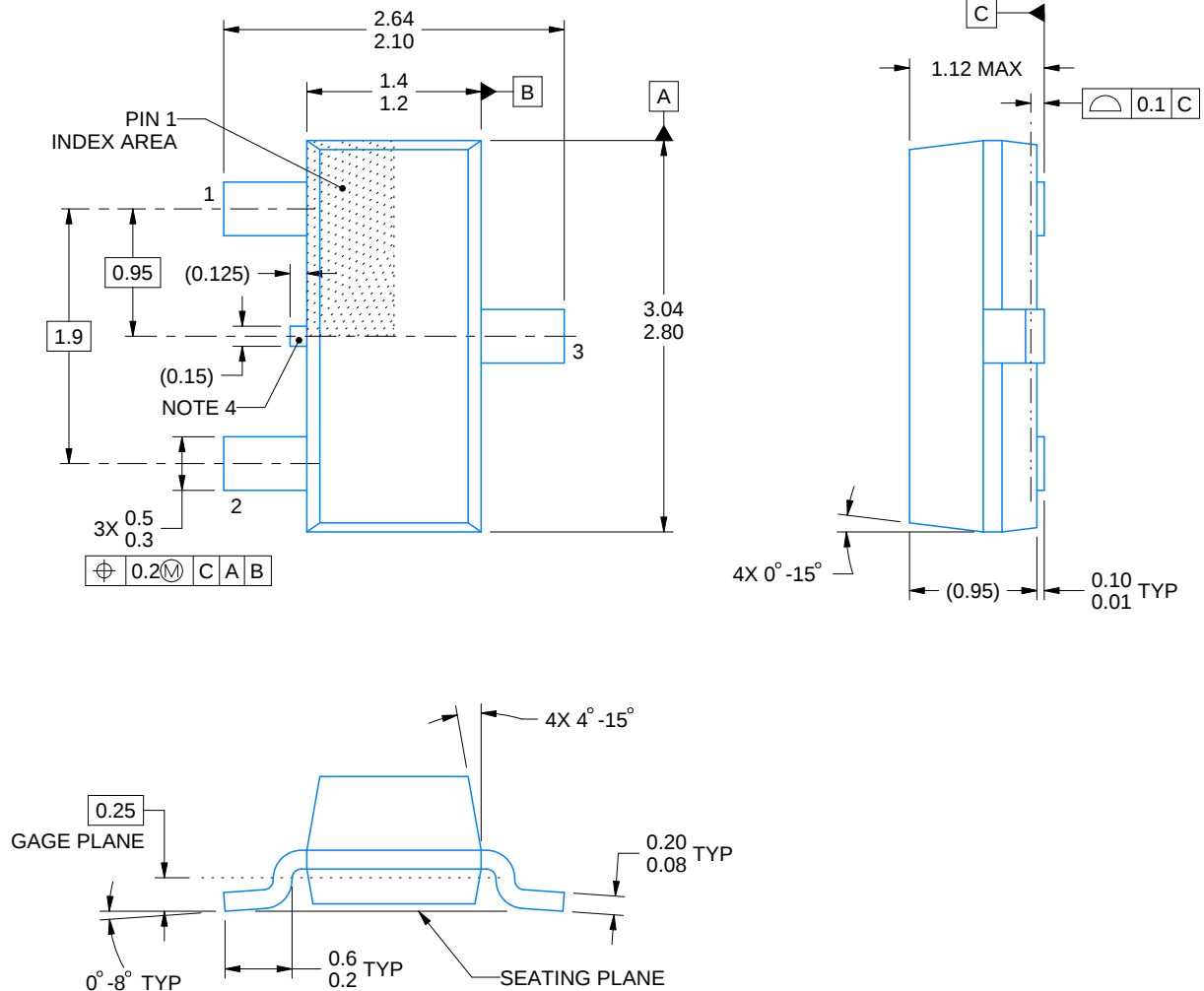


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TMAG5115A1CQDBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TMAG5115B1CQDBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0

DBZ0003A**PACKAGE OUTLINE****SOT-23 - 1.12 mm max height**

SMALL OUTLINE TRANSISTOR



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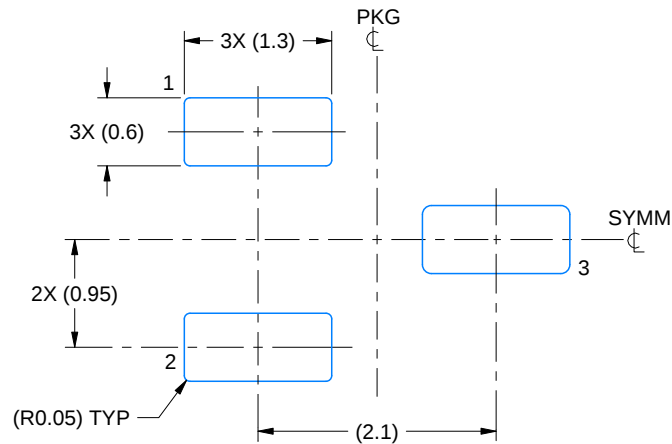
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC registration TO-236, except minimum foot length.
4. Support pin may differ or may not be present.
5. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

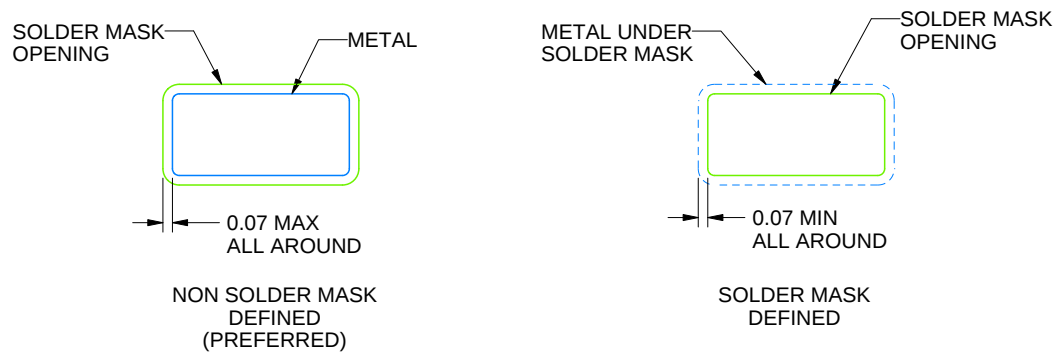
DBZ0003A

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
SCALE:15X



SOLDER MASK DETAILS

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NOTES: (continued)

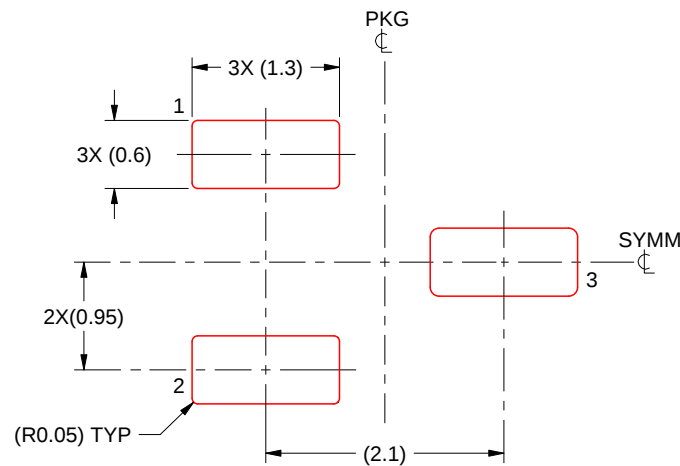
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBZ0003A

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:15X

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NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

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